Title (en)

MEMORY CELL, MEMORY CELL ARRANGEMENT, STRUCTURING ARRANGEMENT AND METHOD FOR PRODUCTION OF A MEMORY CELL

Title (de)

SPEICHERZELLE, SPEICHERZELLEN-ANORDNUNG, STRUKTURIER-ANORDNUNG UND VERFAHREN ZUM HERSTELLEN EINER SPEICHERZELLE

Title (fr)

CELLULE DE MEMOIRE, ENSEMBLE DE CELLULES DE MEMOIRE, ENSEMBLE DE STRUCTURATION ET PROCEDE DE FABRICATION D'UNE CELLULE DE MEMOIRE

Publication

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Application

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Priority

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Abstract (en)

[origin: WO2004040644A2] The invention relates to a memory cell, memory cell arrangement, structuring arrangement and method for production of a memory cell. The memory cell has a vertical gate transistor and a memory capacitor, whereby the vertical gate transistor comprises a semiconducting nanostructure, grown on at least part of the memory capacitor.

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H01L 21/8239

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CPC (source: EP US)

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DOCDB simple family (application)

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